

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU012** is Designed for TV Band IV & V Applications.

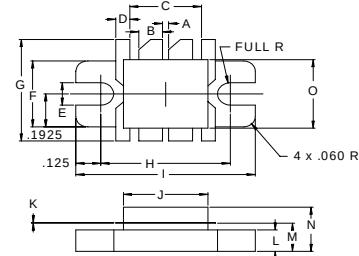
FEATURES:

- Input Matching Network
- Common emitter
- **Omnigold™** Metalization System with eutectic die bonding

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.6 °C/W

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.030 / 0.76
B	.115 / 2.92	.125 / 3.18
C		.360 / 9.14
D	.065 / 1.65	.075 / 1.91
E		.130 / 3.30
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

ORDER CODE: ASI10646

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _E = 28 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
P_G IMD₁	V _{CE} = 26.5 V I _C = 2 X 0.85 mA f = 860 MHz P _{OUT} = 12 W	9.0 -52			dB dBc